CRXSP35M120G4Q

SiC MOSFET 1200V, 35m Ω , 55A

Features

- CRM G4 SIC MOSFET Technology
- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Avalanche Ruggedness
- Fast Reverse Recovery
- AEC-Q101 Qualified

Product Summary

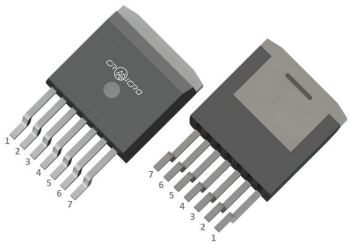
VDS	1200V
$R_{DS(on)_typ}$	35m Ω
I_D	55A

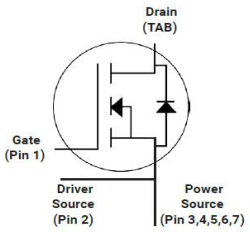
Applications

- Solar Inverters
- High Voltage DC/DC Converters
- On Board Charger(OBC)
- EV Charger

100% Avalanche Tested

RoHS HF





Package Marking and Ordering Information

Part #	Marking	Package	Packing	Qty
CRXSP35M120G4Q	X35M120G4Q	TO-263-7	Reel	800pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	1200	V
Continuous drain current V_{GS}=18V， T_C = 25°C V_{GS}=18V， T_C = 100°C	I_D	 55 39	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D(pulse)}$	138	A
Avalanche energy, single pulse (L=10mH, Rg=25Ω)	E_{AS}	723	mJ
Gate-Source voltage (dynamic)[a1]	V_{GSmax}	-10/+22	V
Gate-Source voltage (static)[a2]	V_{GSop}	-5/+18	V
Power dissipation (T_C=25°C,T_J=175°C)	P_D	208	W
Operating Junction and Storage Temperature	T_j,T_{stg}	-55...175	°C

a1: When using MOSFET Body Diode V_{GSmax} = -5V/+22V

a2: MOSFET can also safely operate at 0/+18V

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction – case. Max	R_{thJC}	0.72	°C/W
Thermal resistance, junction – ambient. Max	R_{thJA}	50	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	$V_{(BR)DSS}$	1200	-	-	V	V_{GS}=0V, I_D=250uA
Gate threshold voltage	$V_{GS(th)}$	2	-	4	V	V_{DS}=V_{GS},I_D=10mA
Zero gate voltage drain current	I_{DSS}	-	0.1	100	μA	V_{DS}=1200V,V_{GS}=0V T_j=25°C
		-	10	-		T_j=175°C
Gate-source leakage current	I_{GSS}	-	-	±100	nA	V_{GS}=-10/+22V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	-	45	56	mΩ	V_{GS}=15V, I_D=22A, T_j=25°C
		-	69	-		T_j=175°C
Drain-source on-state resistance	$R_{DS(on)}$	-	35	46	mΩ	V_{GS}=18V, I_D=22A, T_j=25°C
		-	65	-		T_j=175°C
Transconductance	g_{fs}	-	18	-	S	VDS=20V,IDS=22A
Dynamic Characteristic						
Internal Gate resistance	$R_{G(int)}$	-	3.2	-	Ω	f=1MHz
Input Capacitance	C_{iss}	-	1826	-	pF	V_{GS}=0V, V_{DS}=1000V, f=1MHz
Output Capacitance	C_{oss}	-	72.8	-		
Reverse Transfer Capacitance	C_{rss}	-	4	-		
Coss Stored Energy	E_{oss}	-	45.7	-	uJ	
Gate Total Charge	Q_g	-	79.6	-	nC	VGS=-5/18V VDS=800V ID=22A
Gate-Source charge	Q_{gs}	-	26.9	-		
Gate-Drain charge	Q_{gd}	-	21.3	-		
Turn-on delay time	$t_{d(on)}$	-	9	-	ns	VDD=800V,ID=22A VGS=-5V/18V, RG=2.5Ω, L=120uH
Rise time	t_r	-	12.8	-		
Turn-off delay time	$t_{d(off)}$	-	21.8	-		
Fall time	t_f	-	11.2	-		
Turn-On Switching Energy	$E_{(on)}$	-	93	-	uJ	
Turn Off Switching Energy	$E_{(off)}$	-	84.5	-		

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	4	-	V	V_{GS}=0V,I_F=11A
		-	3.5	-	V	V_{GS}=0V,I_F=11A, T_j=175℃
Continuous Diode Forward Current	I_S	-	-	55	A	V_{GS}=0V
Diode pulse Current	$I_{S,pulse}$	-	-	138	A	pulse width t_p limited by Tjmax
Body Diode Reverse Recovery Time	t_{rr}	-	16	-	ns	di/dt=1000A/us IF=22A Vdd=800V Tj=25℃
Body Diode Reverse Recovery Charge	Q_{rr}	-	140	-	nC	
Body Diode Peak Reverse Recovery Current	I_{rrm}	-	14.8	-	A	
Body Diode Reverse Recovery Time	t_{rr}	-	40.6	-	ns	di/dt=1000A/us IF=22A Vdd=800V, Tj=175℃
Body Diode Reverse Recovery Charge	Q_{rr}	-	280	-	nC	
Body Diode Peak Reverse Recovery Current	I_{rrm}	-	14.8	-	A	

Typical Performance Characteristics

Fig 1. Output Characteristics (Tj=-55℃)

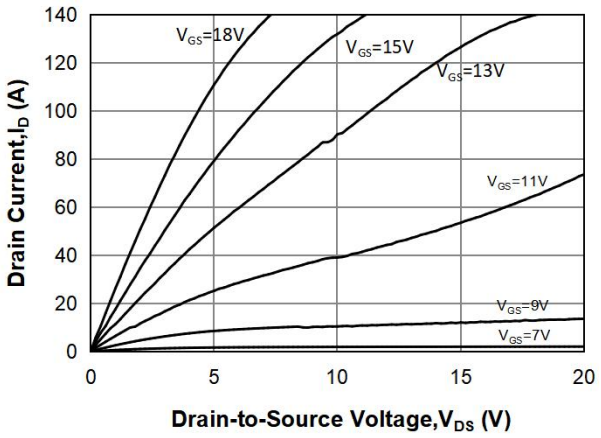


Fig 2. Output Characteristics (Tj=25℃)

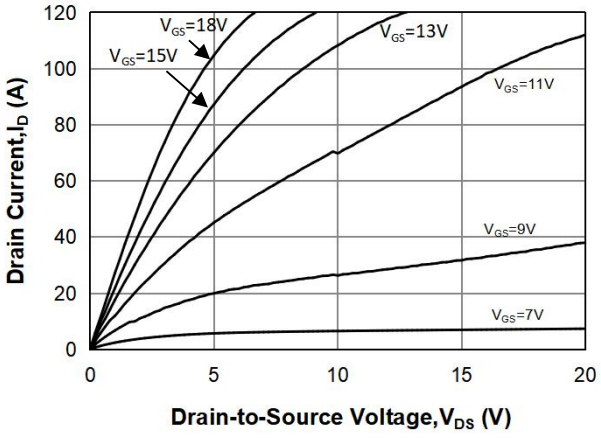


Fig 3. Output Characteristics (Tj=175℃)

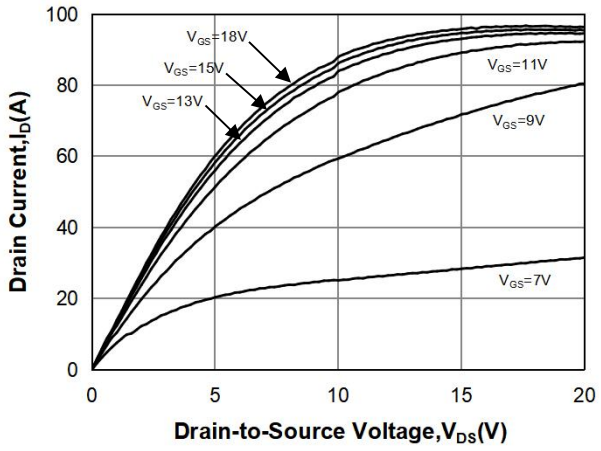


Fig 4: Rds(on) vs. Temperature

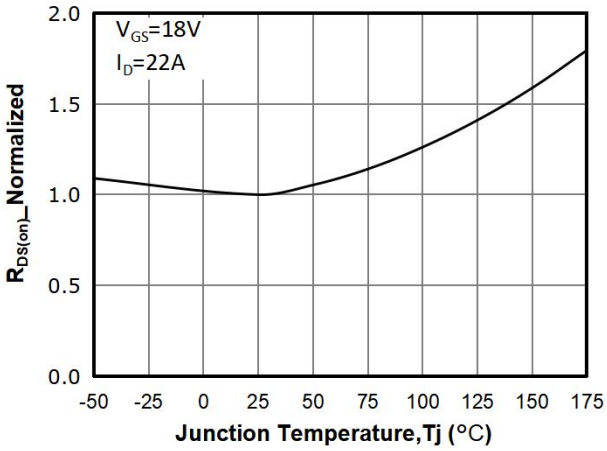


Fig 5: On-Resistance vs. Drain Current For Various Temperatures

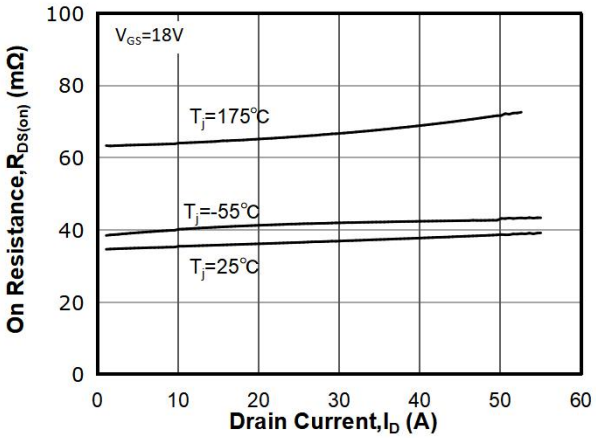


Fig 6: Rds(on) vs. Temperature For Various Gate Voltage

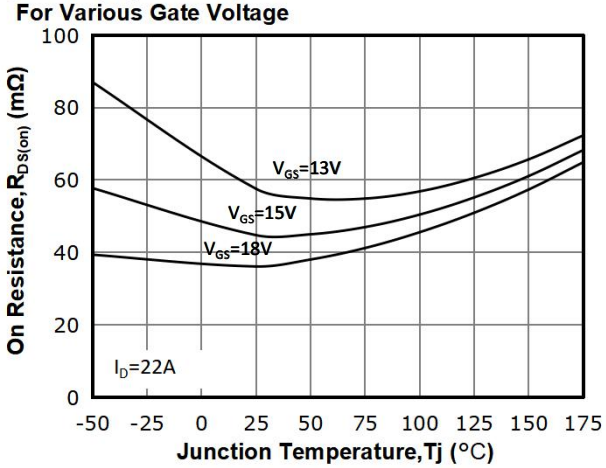


Fig 7: Transfer Characteristics

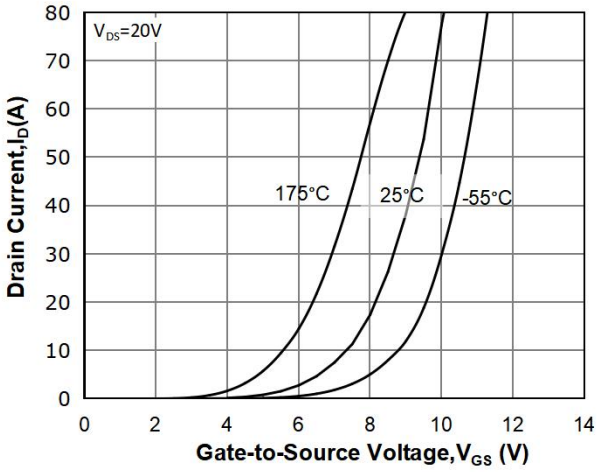


Fig 8: Body-diode Forward Characteristics For Various Temperatures

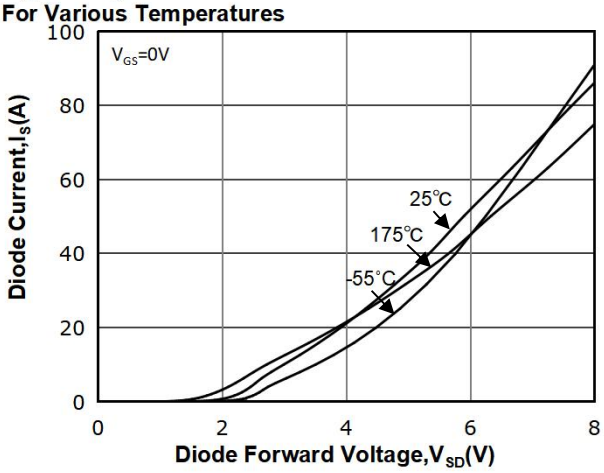


Fig 9: VGS(th) Vs Tj Characteristics

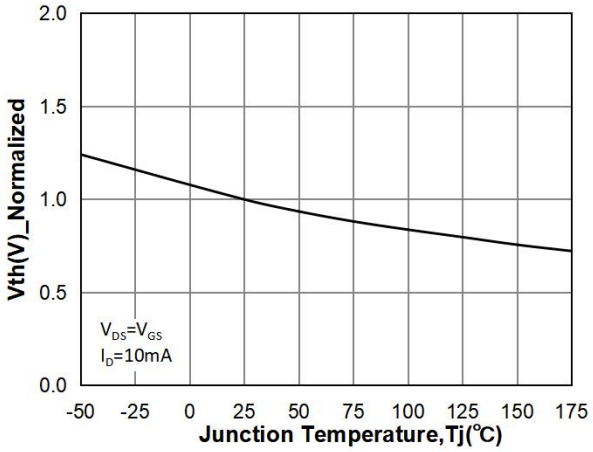


Fig 10: 3rd Quadrant Characteristic at 25℃

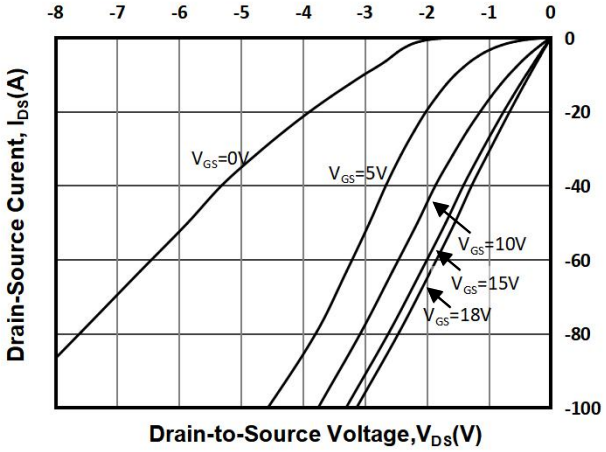


Fig 11：Gtate Charge Characteristics

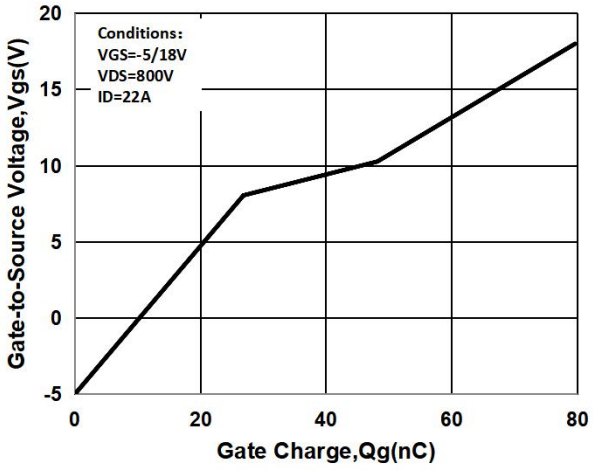


Fig 12: Capacitance Characteristics

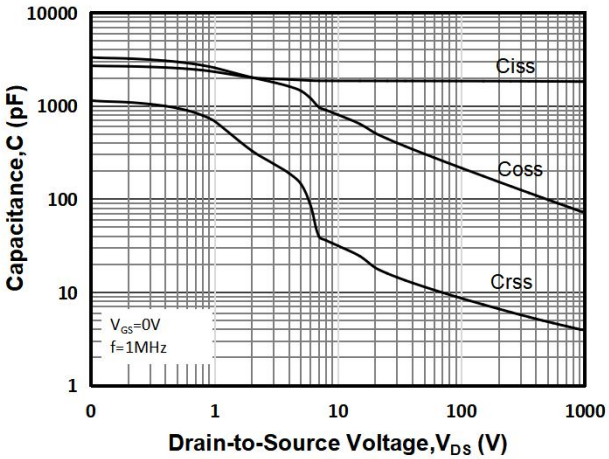


Fig 13: Continuous Drain Current vs. Case Temperature

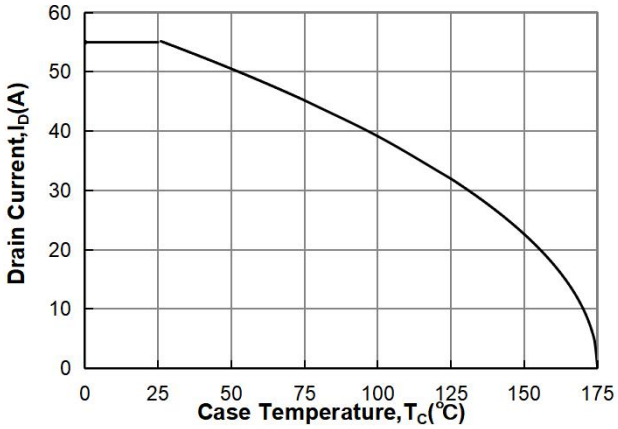


Fig 14: Maximum Power Dissipation vs. Case Temperature

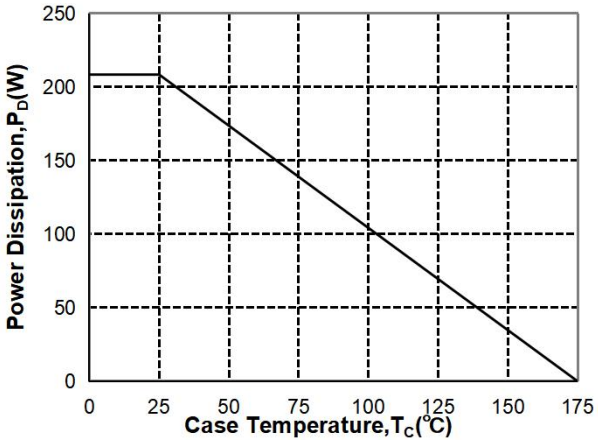


Fig 15: Safe Operating Area

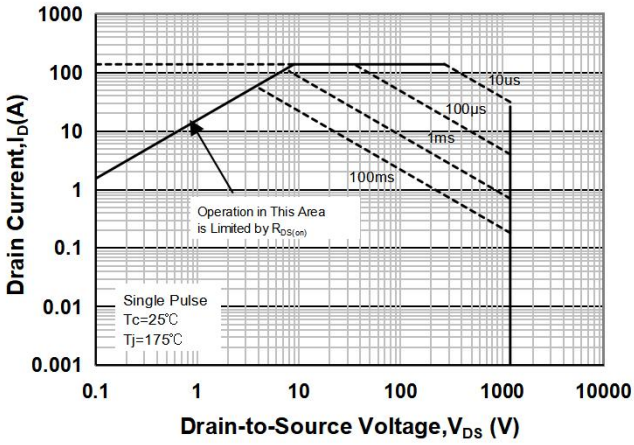


Fig 16:Output Capacitor Stored Energy

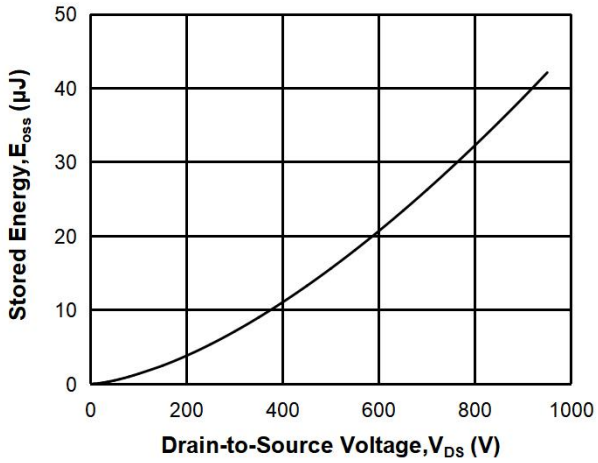


Fig 17: Max. Transient Thermal Impedance

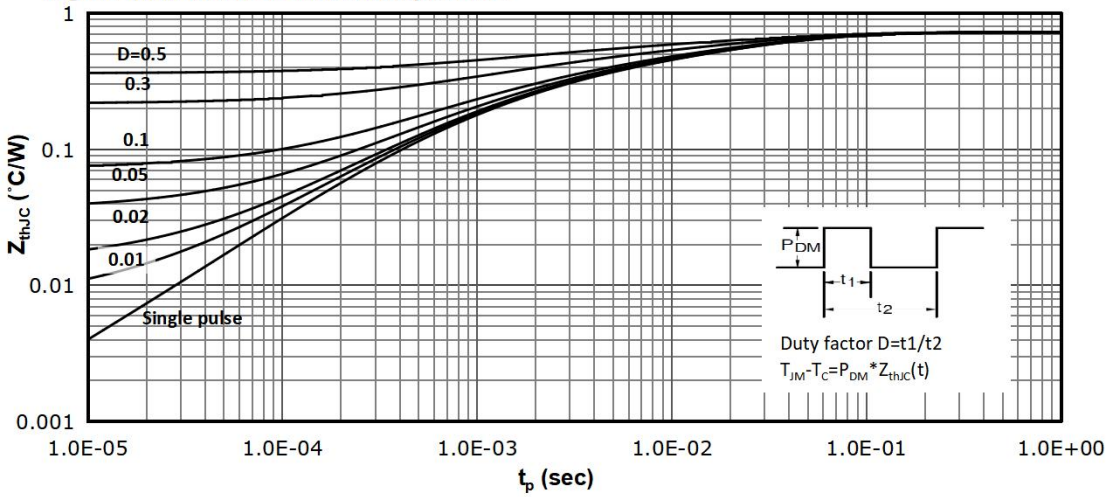


Fig 18: Rg(Ω) vs. Switching Times(us)

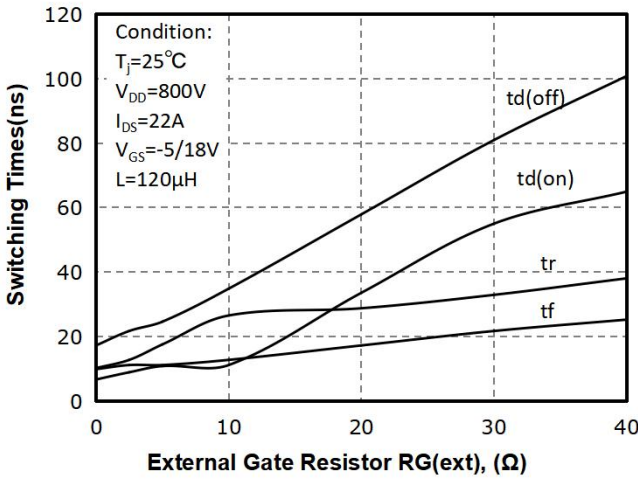


Fig 19: Rg(Ω) vs. Switching Loss(uJ)

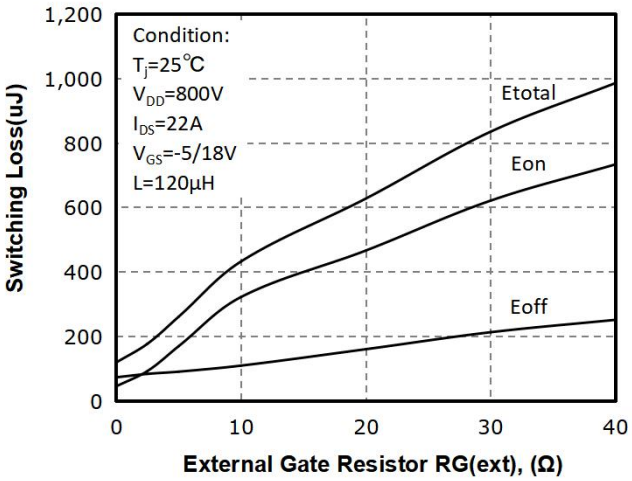


Fig 20: Temperature(°C) vs. Switching Loss(uJ)

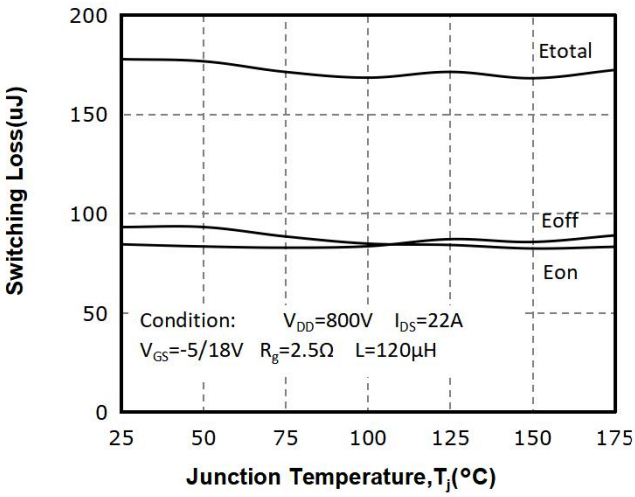
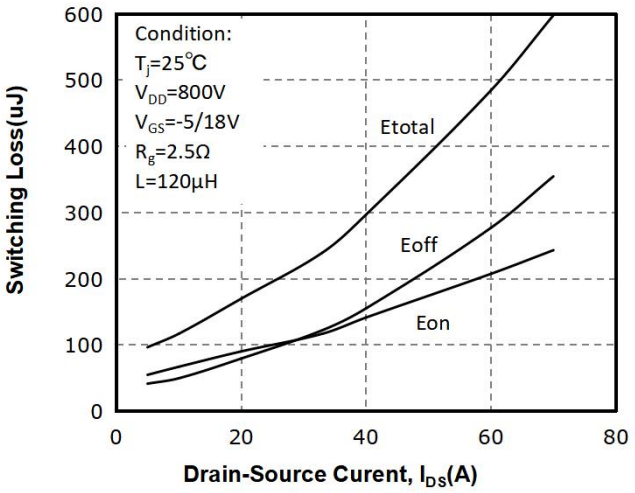
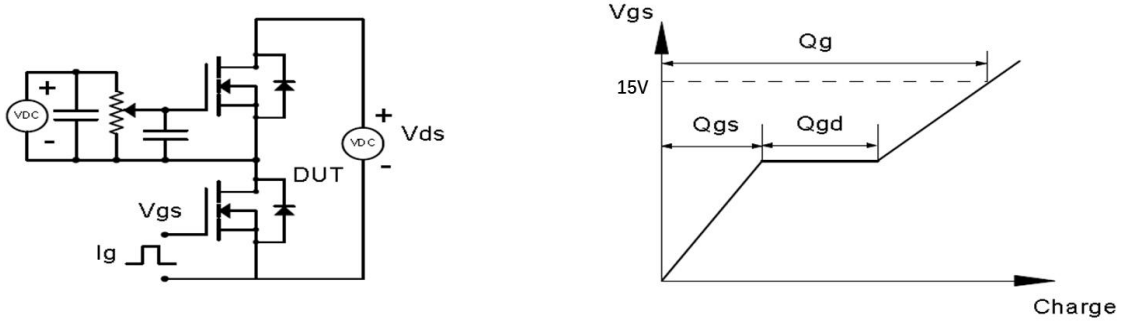


Fig 21: I_{DS}(A) vs. Switching Loss(uJ)

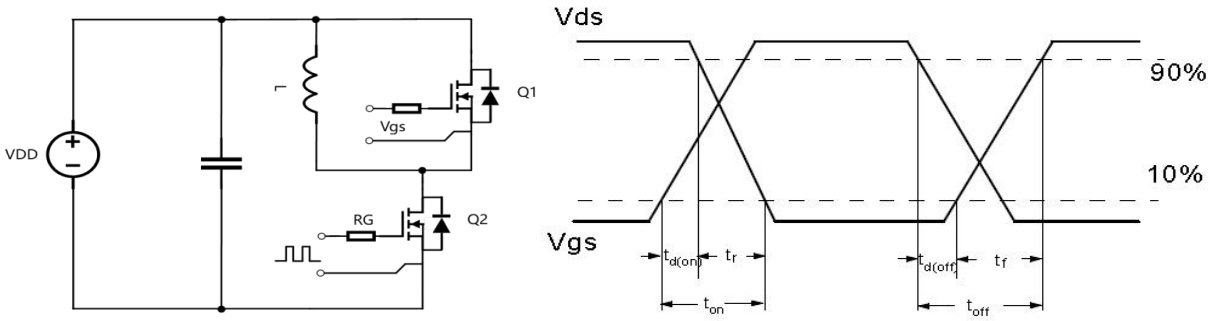


Test Circuit & Waveform

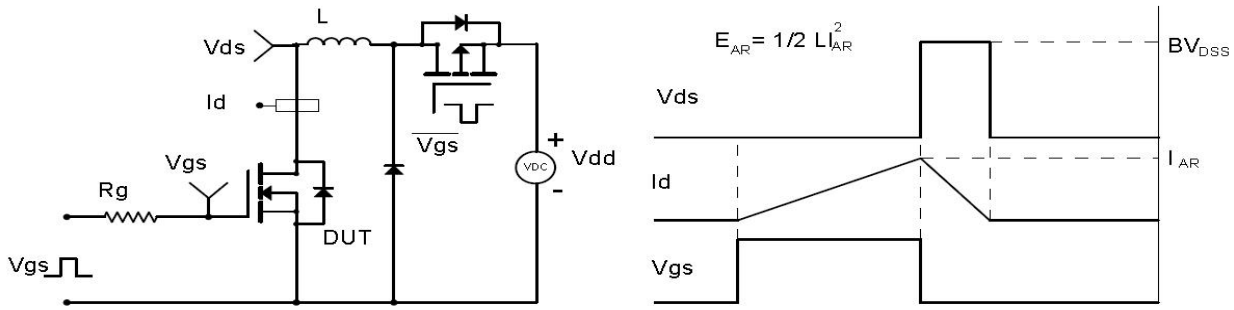
Gate Charge Test Circuit & Waveform



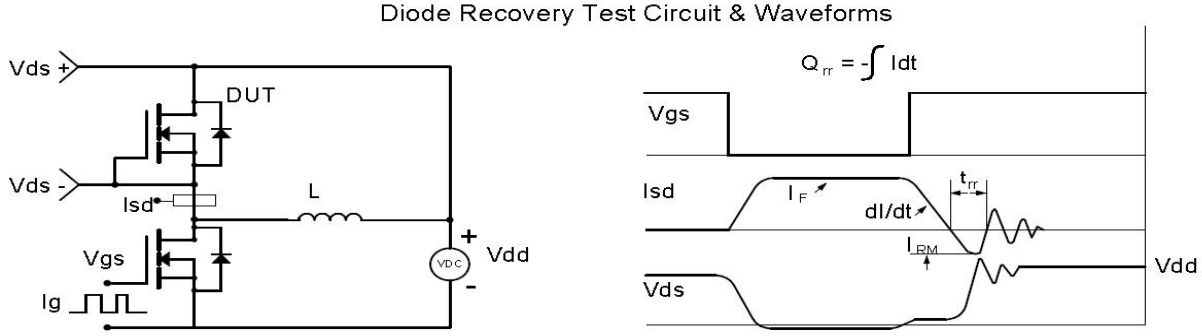
Resistive Switching Test Circuit & Waveforms



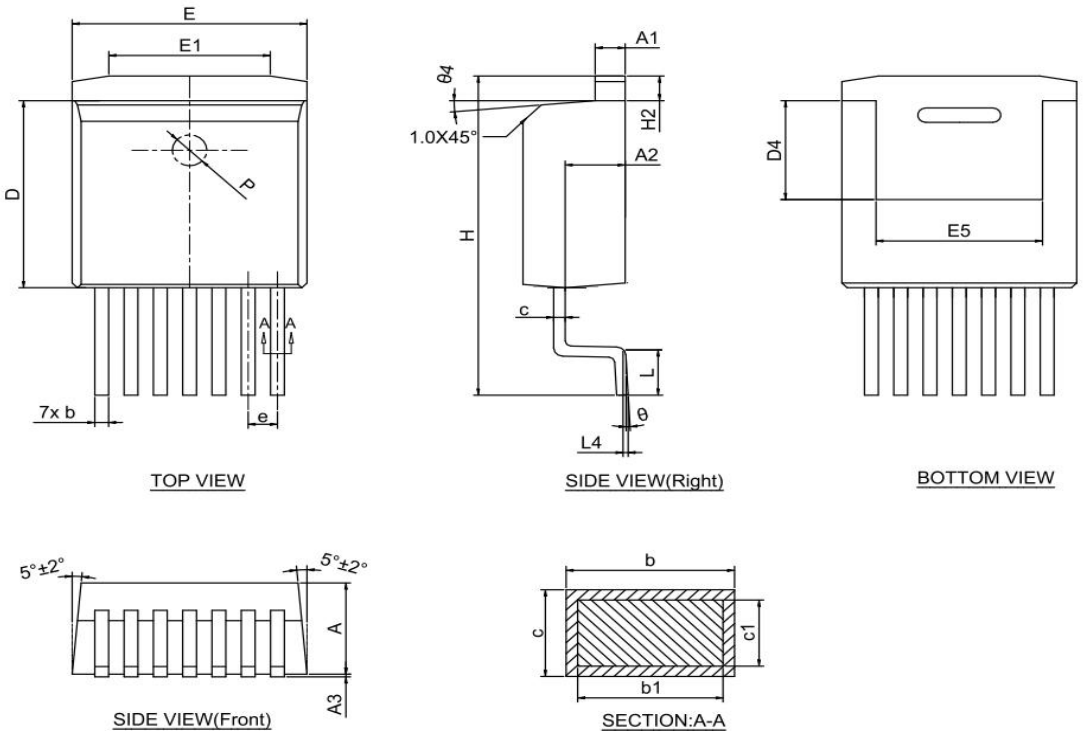
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: TO-263-7



Items	Values(mm)	
	MIN	MAX
A	4.2	4.66
A1	1.15	1.45
A2	2.35	2.85
A3	0	0.3
b	0.5	0.78
b1	0.45	0.75
c	0.49	0.64
c1	0.4	0.6
D	8.83	9.33
D4	4.6	5
e	1.27 BSC.	
E	9.08	10.38
E1	6.4	7.6
E5	6.72	7.72
H	14.9	16.1
H2	0.9	1.45
L	1.8	2.6
L4	0.25 BCS.	
P	1.4	1.6
θ	0°	7°

Revision History

Revison	Date	Major changes
1.0	2025/11/14	Release of formal version
2.0	2026/3/11	Update Ron Spec

Disclaimer

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